

SN74HCS157 Quadruple 2-to-1 Multiplexer with Schmitt-Trigger Inputs

1 Features

- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
 - Typical I_{CC} of 100 nA
 - Typical input leakage current of ±100 nA
- ±7.8-mA output drive at 6 V
- Extended ambient temperature range: -40°C to +125°C, TA

2 Applications

- Data selection
- Multiplexing

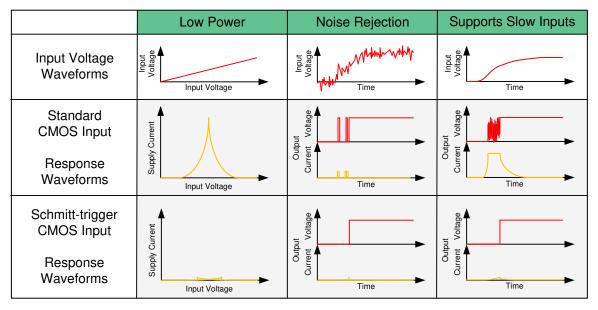
3 Description

The SN74HCS157 contains four data selectors/ multiplexers to select one of two data sources. All channels are controlled by the same address select (\overline{A}/B) input, and strobe (\overline{G}) input. A high level at the strobe terminal forces all outputs low.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)		
SN74HCS157PW	TSSOP (16)	5.00 mm × 4.40 mm		
SN74HCS157D	SOIC (16)	9.90 mm × 3.90 mm		

For all available packages, see the orderable addendum at the end of the data sheet.



Benefits of Schmitt-trigger inputs



Table of Contents

1 Features1	8.3 Feature Description9
2 Applications1	8.4 Device Functional Modes10
3 Description1	9 Application and Implementation11
4 Revision History2	9.1 Application Information11
5 Pin Configuration and Functions3	9.2 Typical Application11
6 Specifications4	10 Power Supply Recommendations14
6.1 Absolute Maximum Ratings4	11 Layout14
6.2 ESD Ratings 4	11.1 Layout Guidelines14
6.3 Recommended Operating Conditions4	11.2 Layout Example14
6.4 Thermal Information4	12 Device and Documentation Support15
6.5 Electrical Characteristics5	12.1 Documentation Support15
6.6 Switching Characteristics5	12.2 Receiving Notification of Documentation Updates 15
6.7 Operating Characteristics6	12.3 Support Resources15
6.8 Typical Characteristics7	12.4 Trademarks15
7 Parameter Measurement Information8	12.5 Electrostatic Discharge Caution15
8 Detailed Description9	12.6 Glossary15
8.1 Reference9	13 Mechanical, Packaging, and Orderable
8.2 Functional Block Diagram9	Information16

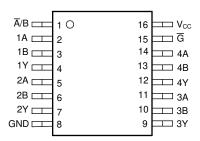
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE REVISION		NOTES		
September 2020	*	Initial Release		



5 Pin Configuration and Functions



D or PW Package 16-Pin SOIC or TSSOP Top View

Pin Functions

PIN			
SOIC or TSSOP NO.	NAME	I/O ⁽¹⁾	DESCRIPTION
1	Ā/B	I	Address select
2	1A	I	Channel 1, data input A
3	1B	I	Channel 1, data input B
4	1Y	I	Channel 1, data output
5	2A	0	Channel 2, data input A
6	2B	0	Channel 2, data input B
7	2Y	I	Channel 2, data output
8	GND	_	Ground
9	3Y	I	Channel 3, data output
10	3B	I	Channel 3, data input B
11	3A	I	Channel 3, data input A
12	4Y	I	Channel 4, data output
13	4B	I	Channel 4, data input B
14	4A	I	Channel 4, data input A
15	G	I	Output strobe, active low
16	V _{CC}	_	Positive supply



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$		±20	mA
Io	Continuous output current	$V_{O} = 0$ to V_{CC}		±35	mA
	Continuous current through V _{CC} or GNE)		±70	mA
TJ	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		-65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±4000	V
	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage	2	5	6	V
VI	Input voltage	0		V _{CC}	V
Vo	Output voltage	0		V _{CC}	V
T _A	Ambient temperature	-40		125	°C

6.4 Thermal Information

		SN74H		
	THERMAL METRIC ⁽¹⁾	PW (TSSOP)	D (SOIC)	UNIT
		16 PINS	16 PINS	
R _{0JA}	Junction-to-ambient thermal resistance	141.2	122.2	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	78.8	80.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	85.8	80.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	27.7	40.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	85.5	80.3	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: SN74HCS157



6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at $T_A = 25$ °C (unless otherwise noted).

	PARAMETER	TEST CO	NDITIONS	V _{cc}	MIN	TYP	MAX	UNIT			
				2 V	0.7		1.5				
V _{T+}	Positive switching threshold			4.5 V	1.7		3.15	V			
				6 V	2.1		4.2				
				2 V	0.3		1.0				
V _{T-}	Negative switching threshold			4.5 V	0.9		2.2	V			
				6 V	1.2		3.0				
				2 V	0.2		1.0				
ΔV_T	Hysteresis (V _{T+} - V _{T-}) ⁽¹⁾			4.5 V	0.4		1.4	V			
				6 V	0.6		1.6				
						I _{OH} = -20 μA	2 V to 6 V	V _{CC} - 0.1	V _{CC} - 0.002		
V _{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}	I _{OH} = -6 mA	4.5 V	4.0	4.3		V			
			I _{OH} = -7.8 mA	6 V	5.4	5.75					
			I _{OL} = 20 μA	2 V to 6 V		0.002	0.1				
V _{OL}	Low-level output voltage	$V_I = V_{IH}$ or V_{IL}	I _{OL} = 6 mA	4.5 V		0.18	0.30	v			
			I _{OL} = 7.8 mA	6 V		0.22	0.33				
I _I	Input leakage current	$V_I = V_{CC}$ or 0		6 V		±100	±1000	nA			
I _{CC}	Supply current	$V_I = V_{CC}$ or 0, I_C	_D = 0	6 V		0.1	2	μA			
Ci	Input capacitance			2 V to 6 V			5	pF			

⁽¹⁾ Guaranteed by design.

6.6 Switching Characteristics

 C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

					Op	erating	free-air	temperat	ure (T _A)		
PARAMETER		FROM TO		V _{cc}	25°C			-40°C to 125°C		°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
				2 V	6			5			
f _{max}	Max switching frequency			4.5 V	31			25			MHz
				6 V	36			29			
				2 V		21	32			55	
		A or B	Y	4.5 V		8	12			19	
				6 V		7	11			16	
		Ā/B	Y	2 V		21	32			57	
t _{pd}	Propagation delay			4.5 V		8	12			20	ns
				6 V		7	11			16	
				2 V		22	33			53	
		G	Υ	4.5 V		9	14			18	
				6 V		8	12			15	
				2 V			13			21	
t _t	Transition-time		Any output	4.5 V			6			9	ns
				6 V			5			7	



6.7 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP	MAX	UNIT
C _{pd}	Power dissipation capacitance per gate	No load	2 V to 6 V		40		pF

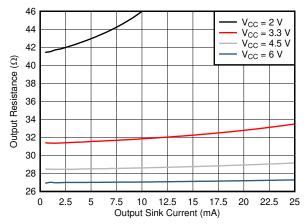
ubmit Document Feedback

Product Folder Links: SN74HCS157



6.8 Typical Characteristics

 $T_A = 25^{\circ}C$



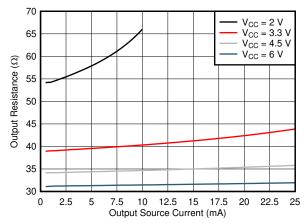
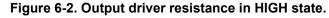
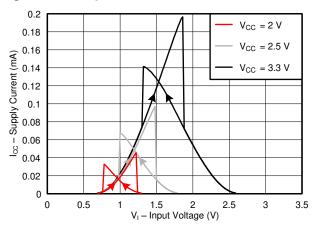


Figure 6-1. Output driver resistance in LOW state.





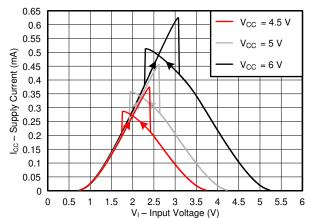


Figure 6-3. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

Figure 6-4. Supply current across input voltage, 4.5-, 5-, and 6-V supply

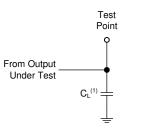


7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_t < 2.5 ns.

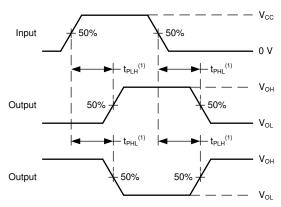
For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



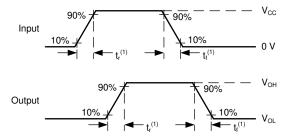
(1) C_L includes probe and test-fixture capacitance.

Figure 7-1. Load Circuit for Push-Pull Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd} .

Figure 7-2. Voltage Waveforms Propagation Delays



(1) The greater between t_{r} and t_{f} is the same as t_{t} .

Figure 7-3. Voltage Waveforms, Input and Output Transition Times



8 Detailed Description

8.1 Reference

The SN74HCS157 is a high speed silicon gate CMOS multiplexer well suited to multiplexing and data routing applications. It contains four 2:1 multiplexers.

The SN74HCS157 operates asynchronously, with each Y output being equal to the input selected by the address input (\overline{A}/B) . All four channels are controlled by the same address input.

The strobe (\overline{G}) input forces all Y outputs low, regardless of the state of other inputs.

All inputs include Schmitt-triggers allowing for slow input transitions and providing additional noise margin.

8.2 Functional Block Diagram

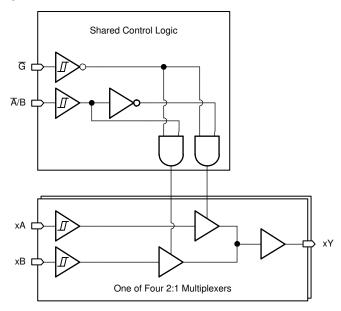


Figure 8-1. Logic Diagram (Positive Logic) for SN74HCS157

8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the



inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

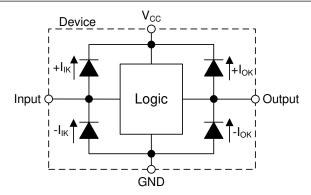


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Function Table lists the functional modes of the SN74HCS157.

Table 8-1. Function Table

	OUTPUT			
G	SELECT	DA	TA	OUIFUI
G	Ā/B	Α	В	Υ
Н	Х	Х	Χ	L
L	L	L	Χ	L
L	L	Н	Χ	Н
L	Н	Х	L	L
L	Н	Х	Н	Н

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care



9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74HCS157 is a quadruple 2-to-1 data selector/multiplexer. This application shows an example of using the device with all required connections to switch a 4-bit data bus between two source devices.

9.2 Typical Application

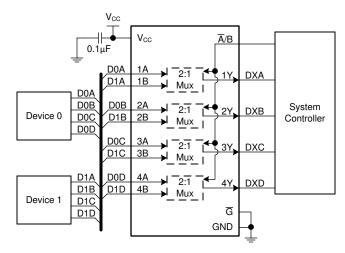


Figure 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS157 plus the maximum static supply current, I_{CC} , listed in *Electrical Characteristics* and any transient current required for switching. The logic device can only source as much current as is provided by the positive supply source. Be sure not to exceed the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS157 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS157 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS157 can drive a load with total resistance described by $R_L \ge V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the high state, the



output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS157, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HCS157 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Feature Description section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS157 to the receiving device(s).

3. Ensure the resistive load at the output is larger than (V_{CC} / I_{O(max)}) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load

measured in megaohms; much larger than the minimum calculated above.

4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curve

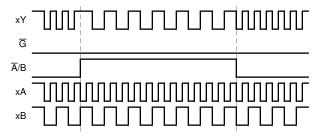


Figure 9-2. Application timing diagram



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

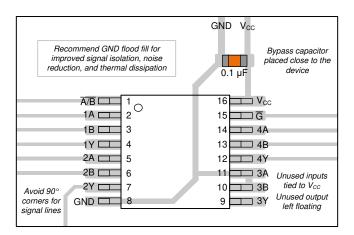


Figure 11-1. Example layout for the SN74HCS157.



12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, HCMOS Design Considerations application report (SCLA007)
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report (SDYA009)
- Texas Instruments, Designing With Logic application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



PACKAGE OPTION ADDENDUM

6-Jan-2021

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HCS157DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS157	Samples
SN74HCS157PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	HCS157	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



PACKAGE OPTION ADDENDUM

6-Jan-2021

OTHER QUALIFIED VERSIONS OF SN74HCS157:

Automotive: SN74HCS157-Q1

www.ti.com

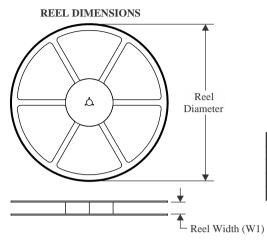
NOTE: Qualified Version Definitions:

• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com 3-Jun-2022

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

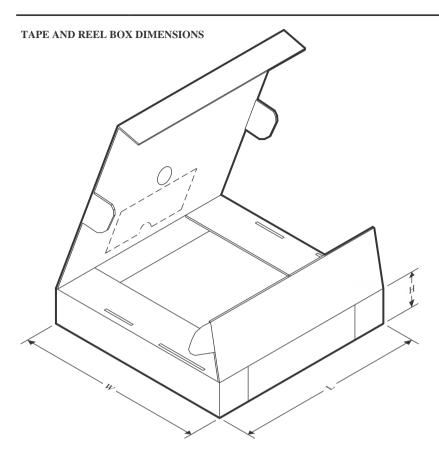
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS157DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN74HCS157DR	SOIC	D	16	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HCS157PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HCS157PWR	TSSOP	PW	16	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1

www.ti.com 3-Jun-2022



*All dimensions are nominal

7 111 01111011010110 0110									
Device	Device Package Type		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN74HCS15	7DR	SOIC	D	16	2500	356.0	356.0	35.0	
SN74HCS15	7DR	SOIC	D	16	2500	366.0	364.0	50.0	
SN74HCS157	'PWR	TSSOP	PW	16	2000	356.0	356.0	35.0	
SN74HCS157	'PWR	TSSOP	PW	16	2000	366.0	364.0	50.0	

D (R-PDS0-G16)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.





SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2022, Texas Instruments Incorporated